R1242S SERIES



30V Input 3A Buck DC/DC converter

NO.EA-191-111123

OUTLINE

The R1242S Series are CMOS-based 30V Input, 3A, Synchronous Rectified Step-down DC/DC Converters with built-in Highside Switch. Each of these ICs contains Nch Highside Tr. (Typ. 0.1Ω) and can supply maximum 3A output current. In order to reduce heat generation caused by energy loss, FET can be used as Lowside switch. Lowside switch turns off when ICs shut down. Each of these ICs consists of the followings: an oscillator, a PWM control circuit, a voltage reference unit, an error amplifier, a phase compensation circuit, a slope control circuit, a soft-start circuit, protection circuits, an internal regulator, a switch, and so on. Also, each of these ICs consists of the following external components: an inductor, resistors, an external FET, and capacitors.

The R1242S Series operates with Current Mode Topology, which does not require any sense resistor. As a result, these ICs can achieve high speed and high efficiency. The oscillator frequencies for each version are set as follows; adjustable between 330kHz to 1000kHz for versions A and B, 330kHz for versions C and D, 500kHz for versions E and F, and 1000kHz for versions G and H.

Each of these ICs are equipped with the protection functions, such as Peak Current Limit function, Latch function, Fold back function, Thermal-Shutdown function, and Undervoltage-Lockout (UVLO) function. Peak Current Limit function restricts the maximum current into 4.5A. Latch function (comes with versions A, C, E, and G) shuts off the output if current limit detection continues for a certain period of time. Fold back function (comes with versions B, D, F, and H) reduces the initial oscillator frequencies into 1/4 when output is short-circuited.

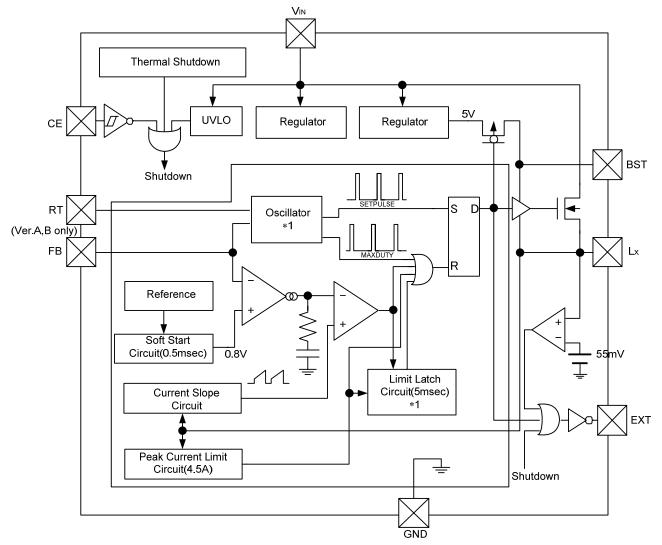
FEATURES

Operating Voltage	5V ~ 30V
Supply Current	Typ. 0.8mA (Set Vouт=1.0V@ViN=30V)
 Internal Nch MOSFET Driver (Ron=100mΩTyp.) 	
• External Nch MOSFET Drive Buffer for Synchronous (Operation
Adjustable Output Voltage with External Resistor	0.8V ~ 15V
Feed Back Voltage	0.8V with 1.5% accuracy
Output Current	3A
Peak Current Limit Function	Typ. 4.5A
UVLO Function	
Internal Soft Start Time	Typ. 0.5ms
Maximum Duty Cycle	
UVLO Detector Threshold	- ·
Thermal Shutdown Function	Typ. 160°C, with 30°C hysteresis
Operating Frequency	
	Version C/D 330kHz
	Version E/F 500kHz Version G/H 1000kHz
Built-in Foldback Protection and its frequency	
Built-ir Foldback Frotection and its frequency	83kHz: Ver.D, 125kHz: Ver.F, 250kHz: Ver.H
Short Protection Function for Internal Boost Regulator	
Short Protection delay time for Output Latch	
Ceramic Capacitor Compatible	
 Stand-by Function: 0μA (Typ.), Max. 20μA (@V_{IN}=30V, 	CE="L")
Package	HSOP-8E

APPLICATIONS

- Power source for digital home appliance
- Power source for hand-held communication equipment, cameras, video instruments such as VCRs, camcorders.
- Power source for battery-powered equipment.
- Battery Charger

Block Diagram



Ver	fosc	Short Protection
Α	Adjustable	Latch
В	Adjustable	Fold back
С	330kHz	Latch
D	330kHz	Fold back
Е	500kHz	Latch
F	500kHz	Fold back
G	1000kHz	Latch
Н	1000kHz	Fold back

Selection Guide

In the R1242 Series, short-circuit protection functions and frequency types can be selected from the followings; Short-circuit protection functions: Latch or Fold back; Frequency types: Adjustable or Fixed. Fixed frequencies are selectable from 330kHz, 500kHz, or 1000kHz.

Product Name	Package	Quantity per Reel	Pb Free	Halogen Free
R1242S001*-E2-FE	HSOP-8E	1,000 pcs	Yes	Yes

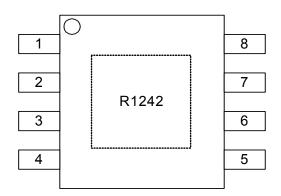
* : Latch or Fold back, frequency can be selected at the user's request

Code	Frequency	Latch Type protection	Fold back Type protection
Α	Adjustable	Yes	No
В	Adjustable	No	Yes
С	330kHz	Yes	No
D	330kHz	No	Yes
Е	500kHz	Yes	No
F	500kHz	No	Yes
G	1000kHz	Yes	No
Н	1000kHz	No	Yes

PIN CONFIGURATIONS

●HSOP-8E

TOP VIEW



PIN DESCRIPTIONS

• R1242S001A/B

PIN No.	Symbol	Description
1	CE	Chip Enable Pin (Active with "H")
2	EXT	Gete Drive Pin
3	BST	Bootstrap Pin
4	VIN	Power Supply Pin
5	Lx	Lx Switching Pin
6	GND	Ground Pin
7	FB	Feedback Pin
8	RT	Frequency Setting Pin

^{*} Tab is GND level. (They are connected to the reverse side of this IC.)

• R1242S001C/D/E/F/G/H

PIN No.	Symbol	Description
1	CE	Chip Enable Pin (Active with "H")
2	EXT	Gate Drive Pin
3	BST	Bootstrap Pin
4	V_{IN}	Power Supply Pin
5	Lx	Lx Switching Pin
6	GND	Ground Pin
7	FB	Feedback Pin
8	TEST	TEST Pin. OPEN or connect to GND

 $[\]ast$ Tab is GND level. (They are connected to the reverse side of this IC.)

^{*} The tab must be connected to the GND.

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Absolute Maximum Ratings

(GND=0V)

Symbol	Item	Rating	Unit
Vin	Input Voltage	-0.3 ~ 32	V
V _{BST}	Boost Pin Voltage	V _L x - 0.3 ~ V _L x + 6	V
VLX	Lx Pin Voltage	-0.3 ~ V _{IN} + 0.3	V
Vce	CE Pin Input Voltage	-0.3 ~ V _{IN} + 0.3	V
V _{FB}	VFB Pin Voltage	-0.3 ~ 6	V
VEXT	EXT Pin Voltage	-0.3 ~ 6	V
V _{RT}	RT Pin Voltage	-0.3 ~ 6	V
Po	Power Dissipation (HSOP-8E) *	2.9	W
Ta	Operating Temperature Range	-40 ~ 85	°C
Tstg	Storage Temperature Range	-55 ~ 125	°C

^{*)} For Power Dissipation, please refer to PACKAGE INFORMATION.

ABSOLUTE MAXIMUM RATINGS

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause the permanent damages and may degrade the life time and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings is not assured.

RECOMMENDED OPERATING CONDITIONS (ELECTRICAL CHARACTERISTICS)

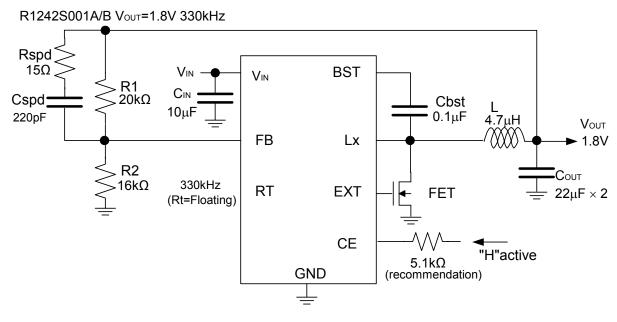
All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if when they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

Electrical Characteristics

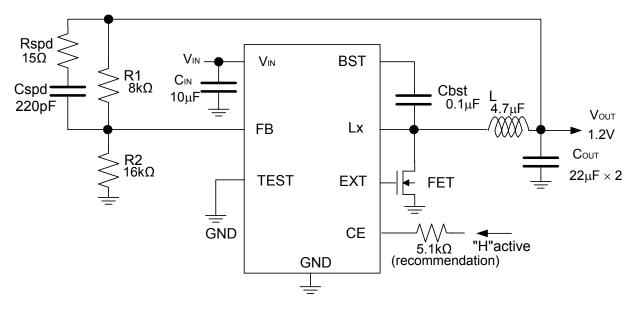
(Otherwise notified in Conditions, VIN= 12V, Ta=25°C)

Symbol	ltem	(Otherwise r	MIN.	TYP.	MAX.	Unit
V _{IN}	Operating Input Voltage		5.0		30	V
I _{IN}	V _{IN} Consumption Current	V _{IN} =30V, V _{FB} =1.0V	0.45	0.80	1.20	mA
V _{UVLO1}	UVLO Detect Voltage	Falling	V _{UVLO2} -0.5		V _{UVLO2} -0.3	V
V _{UVLO2}	UVLO Released Voltage	Rising	3.7	4.0	4.3	V
V _{FB}	VFB Voltage Tolerance		0.788	0.800	0.812	V
ΔV _{FB} /ΔT _a	VFB Voltage Temperature Coefficient	-40°C ≤ Ta ≤ 85°C		±100		ppm/ °C
		RT=GND	900	1000	1100	kHz
	Oscillator Frequency (Ver. A/B)	RT=floating	290	330	375	kHz
fosc		RT=120kΩ	450	500	550	kHz
IOSC	Oscillator Frequency (Ver. C/D)		300	330	370	kHz
	Oscillator Frequency (Ver. E/F)		450	500	550	kHz
	Oscillator Frequency (Ver. G/H)		900	1000	1100	kHz
		V _{FB} <0.56,RT=GND (Ver. B)		250		kHz
V_{FLB}	Fold back Frequency	V _{FB} <0.56 (Ver. D)		83		kHz
VFLB	Fold back Frequency	V _{FB} <0.56 (Ver. F)		125		kHz
		V _{FB} <0.56 (Ver. H)		250		kHz
Maxduty	Max. Duty Cycle	RT=120kΩ (Ver. A/B) V _{IN} =9V (Ver. C/D)	82	88	95	%
tstart	Soft Start Time			0.5		ms
t _{DLY}	Delay Time for Latch Protection	(Ver. A/C/E/G)		5		ms
R _{LXH}	Lx High Side Switch ON Resistance			0.1		Ω
I _{LXHOFF}	Lx High Side Switch Leakage Current			0	20	μΑ
ILIMLXH	Lx High Side Switch Limited Current			4.5		Α
V _{CEH}	CE "H" Input Voltage		1.7			V
V _{CEL}	CE "L" Input Voltage				0.4	V
I _{FB}	VFB Input Current		-1.0		1.0	μΑ
I _{CEH}	CE "H" Input Current		-1.0		1.0	μΑ
I _{CEL}	CE "L" Input Current		-1.0		1.0	μΑ
T _{TSD}	Thermal Shutdown Detect Temperature	Hysteresis 30°C		160		°C
Istandby	Standby Current	V _{IN} =30V, V _{CE} =0V		0	20	μΑ
R _{RISE}	EXT "H" Switch On Resistance	I _{EXT} =-100mA	6		11	Ω
R _{FALL}	EXT "L" Switch On Resistance	I _{EXT} =100mA	0.5		1.5	Ω
V _{EXTLIM}	Detecting Voltage for Low Side Switch Current Limit		36	55	76	mV

Typical application



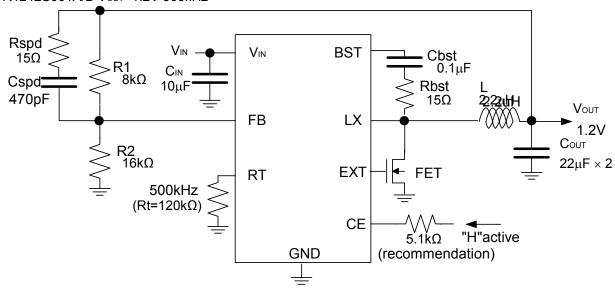
R1242S001C/D Vout=1.2V 330kHz



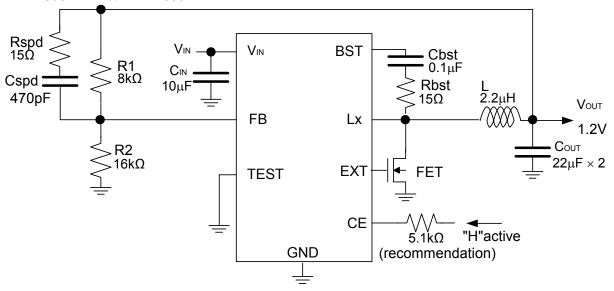
Recommendation parts

Cin	10μF KTS500B106M55N0T00 (Nippon Chemi-Con)
Соит	22μF GRM31CR71A226M (Murata)
Cbst	0.1μF GRM21BB11H104KA01L (Murata)
L	4.7μH VLF10045T-4R7N6R1 (TDK)
FET	TPC8031 (TOSHIBA)

R1242S001A/B Vout=1.2V 500kHz



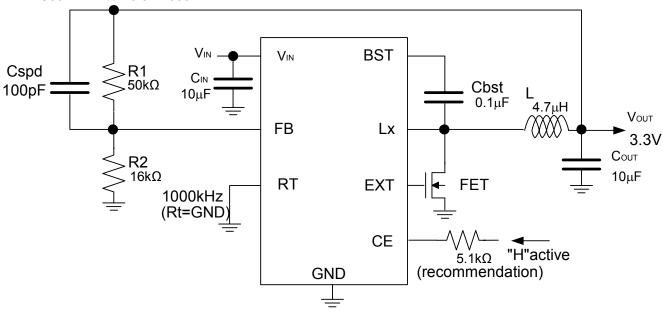
R1242S001E/F Vout=1.2V 500kHz



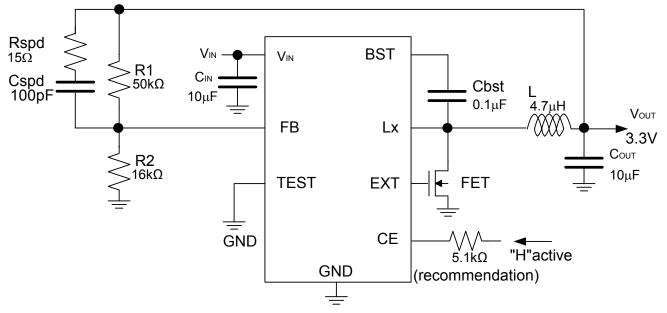
Recommendation parts

Cin	10μF KTS500B106M55N0T00 (Nippon Chemi-Con)
Соит	22μF GRM31CR71A226M (Murata)
Cbst	0.1μF GRM21BB11H104KA01L (Murata)
L	2.2μH RLF7030T-2R2M5R4 (TDK)
FET	TPC8031 (TOSHIBA)

R1242S001A/B Vout=3.3V 1000kHz



R1242S001G/H Vout=3.3V 1000kHz



Recommendation parts

Cin	10μF KTS500B106M55N0T00 (Nippon Chemi-Con)
Соит	10μF GRM31CR71E106K (Murata)
Cbst	0.1μF GRM21BB11H104KA01L (Murata)
L	4.7μH VLF10045T-4R7N6R1 (TDK)
FET	SSM3K14T (TOSHIBA)

Notes Concerning to External Parts

External components must be connected as close as possible to the ICs and their wiring must be short as possible. Especially, the capacitor must be connected with the shortest distance between V_{IN} and GND pins. If the impedances of the power supply line and the GND line are high, the operation can be unstable due to the switching current which fluctuates the electric potential of the inside the ICs. The impedances of power supply line and GND line must be as low as possible. When designing their wirings, it is necessary to give careful consideration to the large current flowing into the power supply, GND, Lx, VouT and inductor. The wiring of output voltage setting resistance (R1) and the wiring of inductor must be separated from load wiring.

The ceramic capacitors with low ESR (Equivalent Series Resistance) must be used for the ICs. The recommended value for the C_{IN} capacitor between V_{IN} and GND is equal or more than $10\mu F$.

The selections of inductor (L) and output capacitor (C_{OUT}) can be different according to the ICs' oscillation frequencies, output voltages and input voltages. Refer to "Recommended Value for Each Output Voltage" on the next page and select the most suitable values at the conditions of use.

The internal phase compensation is built in the ICs; therefore, if the values selected are largely deviated from the recommended values, the operation may result in unstable.

The over current protection circuit could be influenced by self-heating of the ICs and heat dissipation of the PCB environment.

In order to prevent self-turning on, FET with smaller gate resistance and with smaller Cgd / Cgs (capacities between gate drains and the capacities between gate sources) should be selected.

The output voltage (V_{OUT}) can be calculated as $V_{OUT} = V_{FB} \times (R1+R2)/R2$. The various voltage settings are possible by changing the values of R1 and R2. However, R2 value must be equal or less than $16k\Omega$.

Rspd prevents the deterioration in the regulation characteristics, which is caused by spike noise occurred in V_{OUT} . Spike noise is largely depending on the PCB layout. If the PCB board layout is optimized, there is no need of Rspd; however, if the spike noise is a concern, Rspd with 15 Ω or so should be used.

After the completion of soft start, latch function (for versions A, C, E, and G) starts to work. The internal counter starts counting up when the over current protection circuit activates the limited current detection. When the internal counter counts up to 5ms, which is typical latch timer period, latch function turns off the output. The turned off output can be reset when CE pin is changed to "L", and also VIN pin voltage is became less than 3.6V (Typ.), which is UVLO detecting voltage. If the output voltage increases more than the setting voltage (FB pin voltage is 0.8V (Typ.)) within the latch timer period, the counter restores the default. If the power-supply voltage's start-up is slow and the output voltage is not reached to the setting voltage within the latch timer period after the soft start, the careful attention is required.

After the soft start, fold back function (for Version B, D, F, and H) starts to work. The fold back function limits the oscillation frequencies into 1/4 when (FB pin voltage decreases to less than 0.56V (Typ.)). If the power-supply voltage's start-up is slow and the output voltage is not reached to the 70% of the setting voltage even for a short period of time after the soft start, the careful attention is required.

The ICs are not supporting Nonsynchronous rectification using a diode as a rectifier.

The table on the next page shows the recommended values for setting frequency and setting output voltage.



R1242Recommended Value for Each Output Voltage

330kHz

Vout[V]	8.0	1.2	1.2	1.5	1.5	1.8	1.8	2.5	2.5	3.3	5	9	15
V _{IN} _range[V]	5~14	~12	9~30	5~10	10~30	5~15	12~30	5~15	12~30	5~30	7~30	15~30	20~30
L[μH]	2.2	10	4.7	10	4.7	15	4.7	15	10	15	15	15	15
Cουτ[μF]	100	22	44	22	44	22	44	22	22	22	22	22	22
Cspd[pF]	-	470	470	220	220	470	220	220	220	220	220	220	220->100
R1[Ω]	-	8000	8000	14000	14000	20000	20000	34000	34000	50000	84000	164000	284000
R2[Ω]	-	16000	16000	16000	16000	16000	16000	16000	16000	16000	16000	16000	16000

500kHz

Vout[V]	8.0	1.0	1.2	1.5	1.5	1.8	1.8	2.5	3.3	5	9	12	15
V _{IN} _range[V]	~9	~10	5~15	5~18	7~19	5~23	9~21	5~29	5~30	7~30	15~30	18~30	20~30
L[μH]	2.2	2.2	2.2	4.7	2.2	4.7	2.2	10	10	10	10	15	15
Сουτ[μF]	100	44	44	44	44	44	44	22	22	22	22	22	22
Cspd[pF]	-	1000	470	220	220	220	220	220	220	220	220	470	220
R1[Ω]	-	4000	8000	14000	14000	20000	20000	34000	50000	84000	164000	28000	284000
R2[Ω]	-	16000	16000	16000	16000	16000	16000	16000	16000	16000	16000	2000	16000

1000kHz

Vout[V]	0.8	1.2	1.5	1.8	2.5	3.3	5	5	9	15
V _{IN} _range[V]	5~7	5~10	5~15	5~15	5~19	5~30	7~12	12~30	15~30	20~30
L[μH]	1.5	2.2	2.2	4.7	4.7	4.7	4.7	4.7	4.7	10
Сουτ[μF]	100	22	22	22	22	10	10	10	10	10
Cspd[pF]	-	220	100	220	220	100	100	56	56	100
R1[Ω]	-	8000	14000	20000	34000	50000	84000	84000	164000	284000
R2[Ω]	-	16000	16000	16000	16000	16000	16000	16000	16000	16000

R1242Recommendation parts

Symbol	Condition	Value	Parts Name	MFR					
Cin		10μF/50V	UMK325BJ106MM-T	TAIYO YUDEN					
		10μF/50V	KTS500B106M55N0T00	Nippon Chemi-Con					
		10μF/10V	GRM31CR71A106K	muRata					
Соит	Vоит>10V	10μF/50V	KTS500B106M55N0T00	Nippon Chemi-Con					
	10V>Vоит>1.8V	10μF/25V	GRM31CR71E106K	muRata					
	Vоит<1.8V	22μF/10V	GRM31CR71A226M (at the diode rectifier, the specified condition only)	muRata					
Cbst		0.1μF/50V	GRM21BB11H104KA01L	muRata					
L	1.5μH±30%/4.0A	1.5μΗ	SLF7055T-3PF-1R5N4R0	TDK					
	2.2μH±20%/5.4A	2.2μΗ	RLF7030T-2R2M5R4	TDK					
	4.7μH±30%/6.1A	4.7μΗ	VLF10045T-4R7N6R1	TDK					
	10μH±20%6.2A	10μΗ	VLF12060T-100M6R2	TDK					
	15μH±20%5.0A	15μΗ	VLF12060T-150M5R0	TDK					
FET	30V/4A	57mΩ	SSM3K14T	TOSHIBA					
	30V/13A	14.3mΩ	TPCC8003-H	TOSHIBA					
	30V/11A	9.8mΩ	TPCP8005-H	TOSHIBA					
	30V/11A	10.1mΩ	TPC8031-H	TOSHIBA					
RCE	Up Diode is connected between CE pin and V _{IN} pin as an ESD protection element.								
	If there is a possibility that the CE pin voltage becomes higher than the V _{IN} pin voltage,								
	it is recommended to insert a $5k\Omega$ resistance or more in order to prevent the large current								
	flowing from CE pin into V _{IN} pin.								

Operating Frequency

In the application circuit of the R1242S001A/B, the 330kHz operation is selected by leaving Rt open. Connecting a $200k\Omega$ to 0Ω resistor between Rt(pin 8) and ground can be used to set the switching frequency to approximately 450kHz to 1000kHz. To calculate the Rt resistor, use the equation below:

*(Between 330kHz and 450kHz switching frequency can be also set by connecting the appropriate resistor according to the next equation.)

Rt=120000/(2/(1000000/fosc-1)-1) [Ω]

The switching frequency vs. Rt value is shown in Figure 1 and Figure 2.

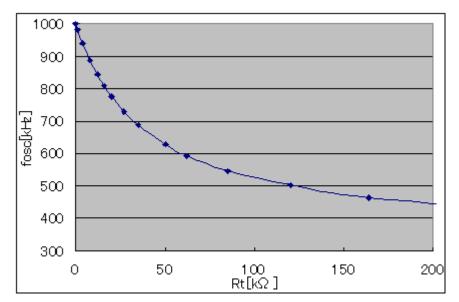


Figure 1: Linearscale

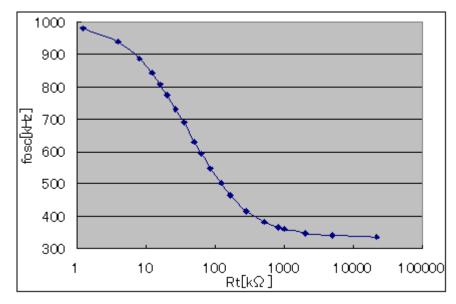


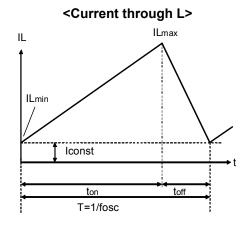
Figure 2: Logscale

Operation of step-down DC/DC converter and Output Current

The DC/DC converter charges energy in the inductor when Lx transistor is ON, and discharges the energy from the inductor when Lx transistor is OFF and controls with less energy loss, so that a lower output voltage than the input voltage is obtained. The operation will be explained with reference to the following diagrams:

VIN Hiside Tr L Lowside FET 12 TCOUT

<Basic Circuit>



- Step1. Hiside Tr. Turns on and current IL (=i1) flows, and energy is charged into C_{OUT}. At this moment, IL increases from ILmin to reach ILmax in proportion to the on-time period (ton) of Hiside Tr.
- Step2. When Hiside Tr. Turns off, Synchronous rectifier Lowside FET turns on in order that L maintains IL at ILmax, and current IL (=i2) flows.
- · Step3. IL decreases from ILmax to reach ILmin in proportion to the off-time period (toff) of Hiside Tr.

GND

In the case of PWM control system, the output voltage is maintained by controlling the on-time period (ton), with the oscillator frequency (fosc) being maintained constant.

The maximum value (ILmax) and the minimum value (ILmin) of the current flowing through the inductor are the same as those when Hiside Tr. Turns on and off.

Output Current and selection of External components

The relation between the output current and external components is as follows:

When Hiside Tr. Of Lx is ON:

(Wherein, Ripple Current p-p value is described as IRP, ON resistance of Hiside Tr. And Lowside FET of Lx are respectively described as Ronh and Ronl, and the DC resistor of the inductor is described as RL.)

When Hiside Tr. Of Lx is "OFF" (Lowside FET is "ON"):

Put Equation 2 to Equation 1 and solve for ON duty of Hiside Tr., $D_{ON} = ton / (toff + ton)$,

Don =
$$(V_{OUT} + (R_{ONL} + R_L) \times I_{OUT})/(V_{IN} + (R_{ONL} - R_{ONH}) \times I_{OUT})$$
..... Equation 3

Ripple Current is as follows:

$$I_{RP} = (V_{IN} - V_{OUT} - R_{ONH} \times I_{OUT} - R_{L} \times I_{OUT}) \times D_{ON} / f_{OSC} / L$$
 Equation 4

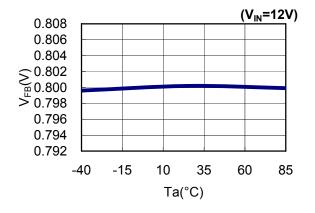
wherein, peak current that flows through inductor, Hiside Tr, and Lowside FET is as follows:

Consider ILmax, condition of input and output and select external components.

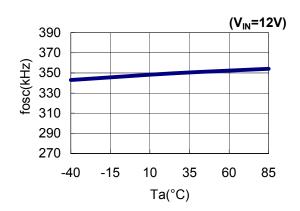
*The above explanation is directed to the calculation in an ideal case in continuous mode.

TYPICAL CHARACTERISTICS

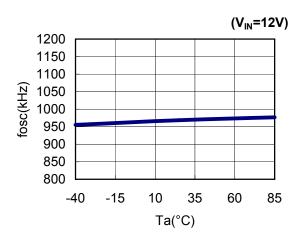
1)FB Voltage



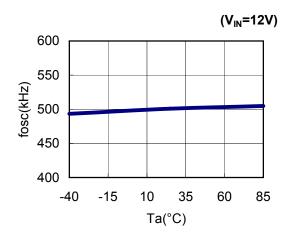
2)Oscillator Frequency(ver.A,B Rt=floating)



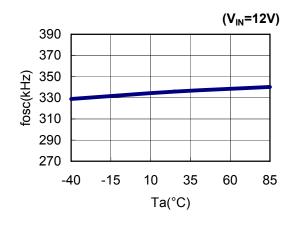
3)Oscillator Frequency(ver.A,B Rt=GND)



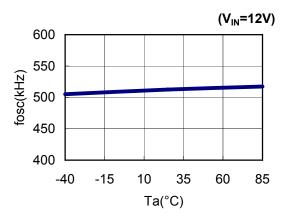
4)Oscillator Frequency(ver.A,B Rt=120kΩ)



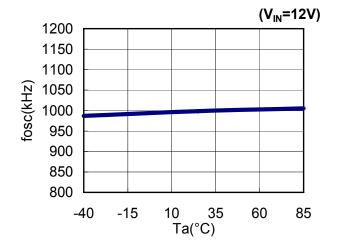
5)Oscillator Frequency(ver.C,D)



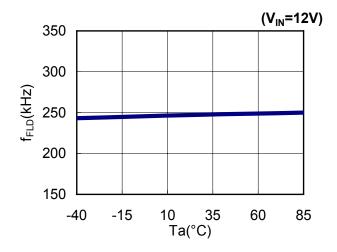
6) Oscillator Frequency(ver.E,F)



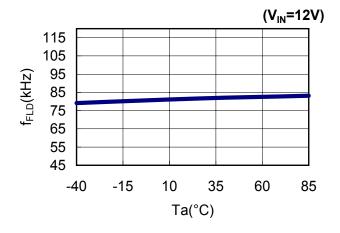
7) Oscillator Frequency(ver.G,H)



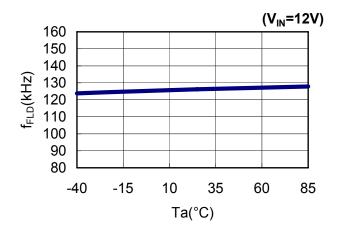
8) Fold-Back Frequency(ver.A,B Rt=GND)



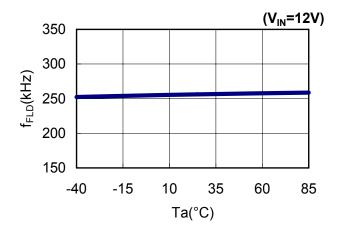
9) Fold-Back Frequency(ver.C,D)



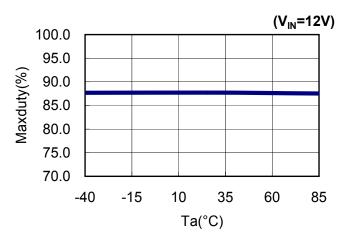
10) Fold-Back Frequency(ver.E,F)



11) Fold-Back Frequency(ver.G,H)

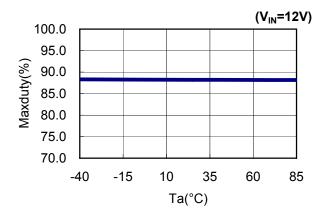


12) Maxduty(ver.A,B Rt=floating)

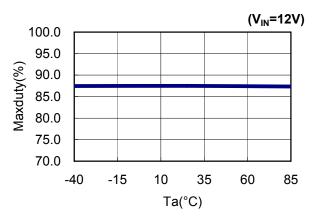


R1242S

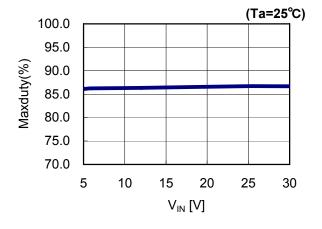
13) Maxduty(ver.C,D)



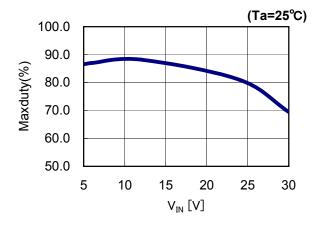
14) Maxduty(ver.G,H)



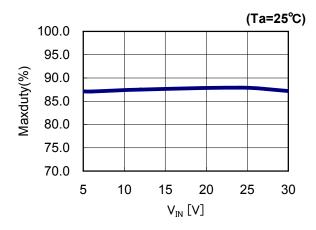
15) Maxduty(ver.A,B Rt=GND)



16) Maxduty(ver.C,D)

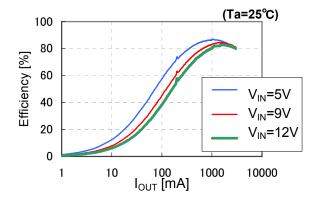


17) Maxduty(ver.G,H)

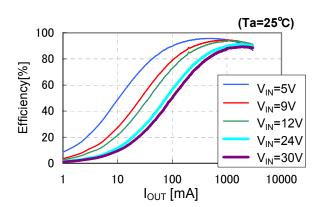


18)Efficiency vs Load Current fosc=330kHz

V_{OUT}:0.8V

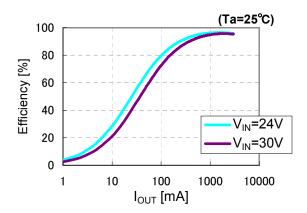


V_{OUT}:3.3V

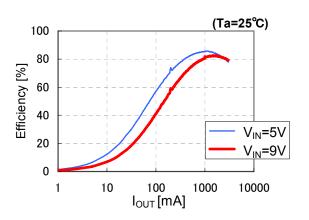


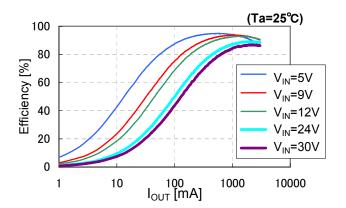
V_{OUT}:15V

fosc=500kHz V_{OUT}:0.8V

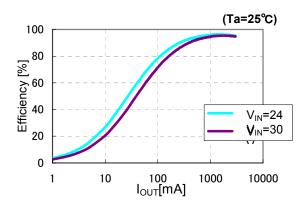


 $V_{OUT}:3.3V$



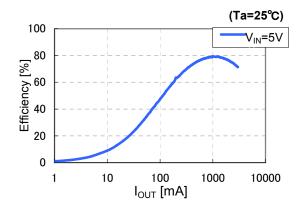


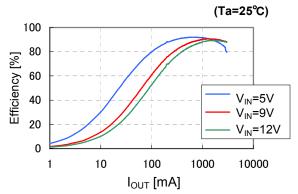
V_{OUT}:15V



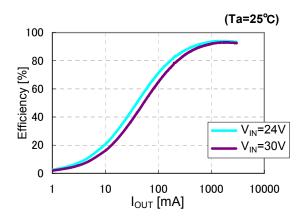
fosc=1000kHz V_{OUT}:0.8V

V_{OUT}:3.3V



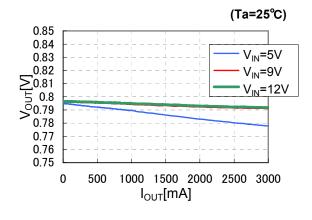


V_{OUT}:15V

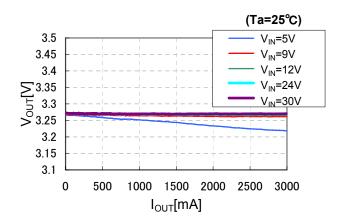


19)Load Regulation fosc=330kHz

V_{OUT}:0.8V

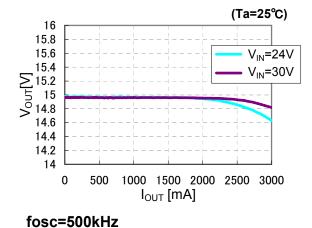


V_{OUT}:3.3V

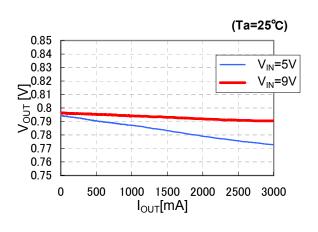


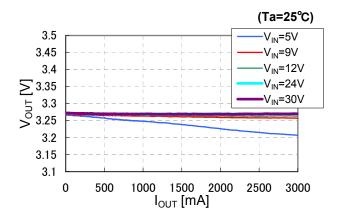
V_{OUT}:15V

 $V_{OUT}:0.8V$

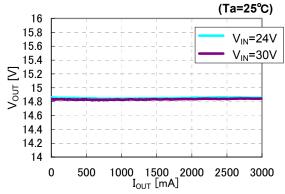


V_{OUT}:3.3V



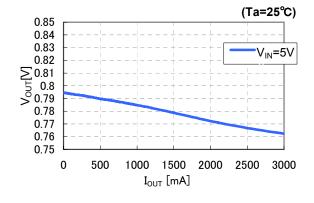


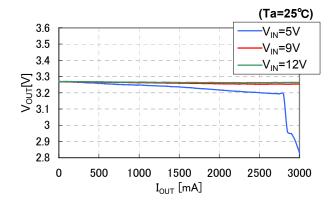
V_{OUT}:15V



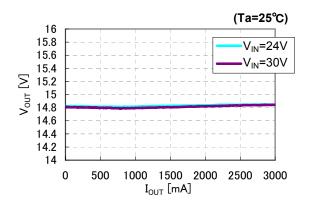
fosc=1000kHz V_{OUT}:0.8V

V_{OUT}:3.3V





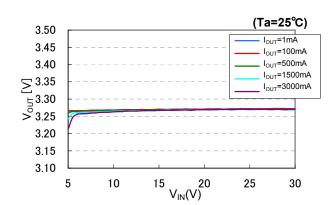
V_{OUT}:15V



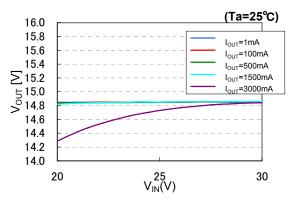
20)Line Regulation fosc=330kHz V_{OUT}:0.8V

(Ta=25°C) 0.85 I_{OUT}=1mA 0.84 I_{OUT}=100mA 0.83 I_{OUT}=500mA ∑ 0.82 0.81 I_{OUT}=1500mA _{Iоит}=3000mA 5 0.80 > 0.79 0.78 0.77 0.76 0.75 $^{15}V_{IN}(V)^{20}$ 5 10 25 30

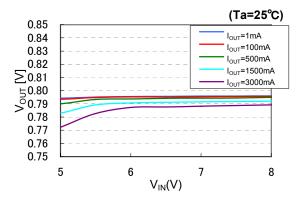
V_{OUT}:3.3V



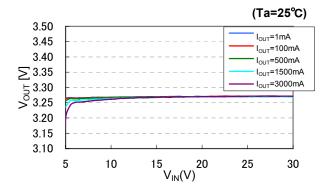
V_{OUT}:15V



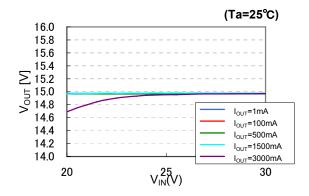
fosc=500kHz V_{OUT}:0.8V



V_{OUT}:3.3V



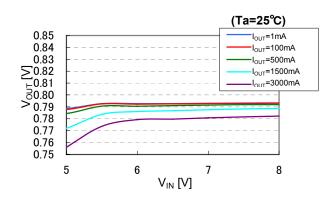
V_{OUT}:15V

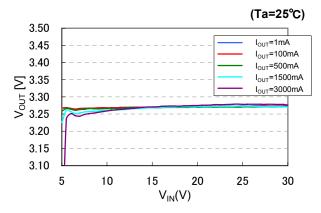


fosc=1000kHz

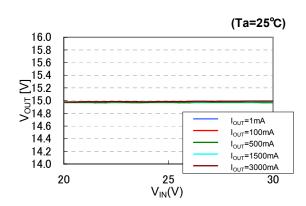
 $\textbf{V}_{\text{OUT}}\textbf{:}\textbf{0.8V}$

V_{OUT}:3.3V





V_{OUT}:15V





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After Apr. 1, 2006, we will ship out the lead free products only. Thus, all products that will be shipped from now on comply with RoHS Directive.